

## Simple Monte Carlo Simulator

### 1. Introduction:

The Simple Monte Carlo simulator is a standalone executable written in C++ to allow for the Simple Monte Carlo modelling of Avalanche Photodiodes and Single Photon Avalanche photodiodes.

#### a) Current Materials available:

- Silicon (Si)
- Indium Gallium Phosphide (InGaP)
- Gallium Arsenide (GaAs)

#### b) Capable of simulating:

- Gain
- Excess Noise Factor
- Breakdown Probability
- Time to Breakdown
- Timing Jitter
- Drift Velocity
- Ionization Coefficients

### 2. Software Links:

GitHub Repository: TBD

Archived Copy vTBD: TBD

Software Metapaper: TBD

### 3. Modes:

There are three simulation modes in the software:

Mode	Capabilities
Diode Properties	<ul style="list-style-type: none"><li>• Gain</li><li>• Excess Noise Factor</li><li>• Breakdown Probability</li><li>• Time to Breakdown</li></ul>
Drift Velocity	<ul style="list-style-type: none"><li>• Electron Drift Velocity</li><li>• Hole Drift Velocity</li></ul>
Impact Ionization Coefficients	<ul style="list-style-type: none"><li>• Electron Coefficient</li><li>• Hole Coefficient</li></ul>

#### 4. Use of Diode Properties Mode:

##### a) Setup

Before launching the executable two text files need to be created:

- 1) *doping\_profile.txt*, which contains the doping of the device to be simulated.

The N-type region must be specified first. Doping concentrations to be specified in atoms/cm<sup>3</sup> and widths to be specified in μm. See example below for a P-I-N device with an N-type I region that's 0.13 μm.

```
-3e18
-2e16, 0.13
3e18
```

The built in Poisson equation solver can work with an infinite number of layers, and it will always ignore the specified width of the 1<sup>st</sup> and last region specified.

- 2) *bias\_input.txt*, which contains a list of applied biases to simulate. Only put 1 bias per line.

##### b) Running the Software

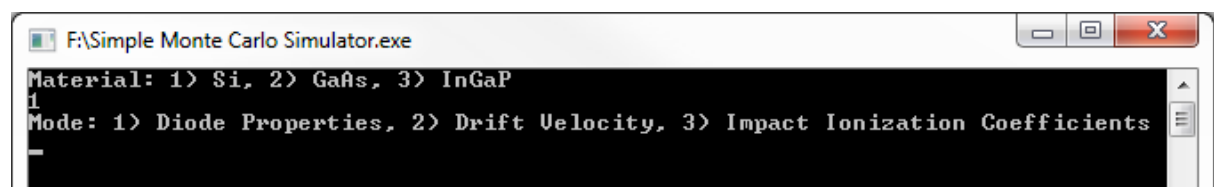
Launch the executable

Program will prompt for a material choice:



```
F:\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
_
```

Program will then prompt for a mode choice. Enter 1 for Diode Properties.

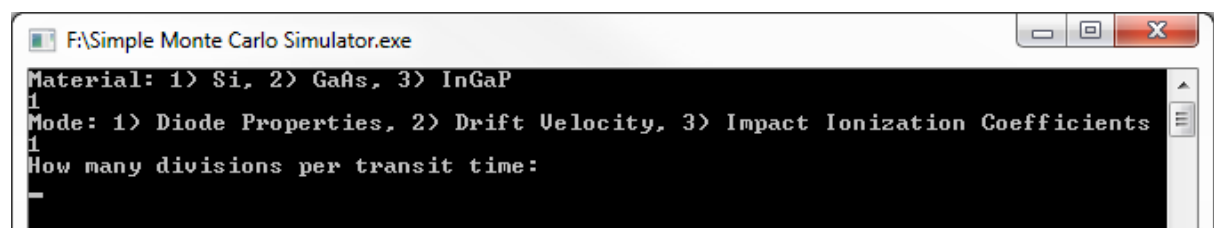


```
F:\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
_
```

Program will then prompt for a number of divisions per transit time. This decides size of the time bins. It is calculated as below

$$\text{Bin Width} = \frac{\text{Time for electron at saturation velocity to cross depletion width}}{\text{Number of Divisions}}$$

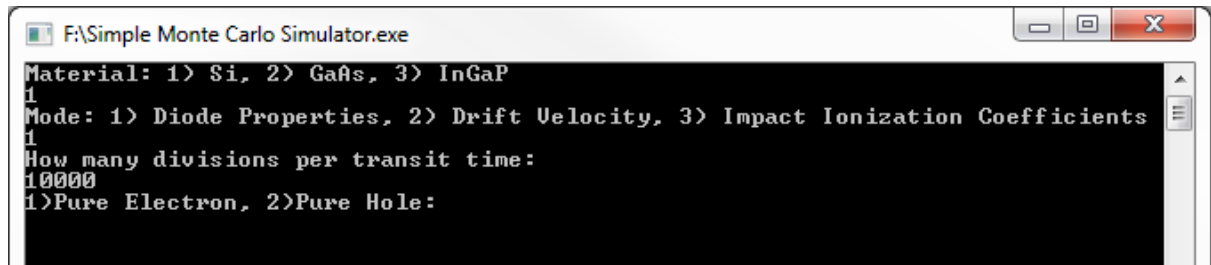
A typical value would be 10000.



```
F:\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
1
How many divisions per transit time:
_
```

Next the Program will prompt for the injection condition:

Number	Condition	Description
1	Pure Electron	Injects a Single electron at the P-Region edge.
2	Pure Hole	Injects a Single hole at the N-Region edge.

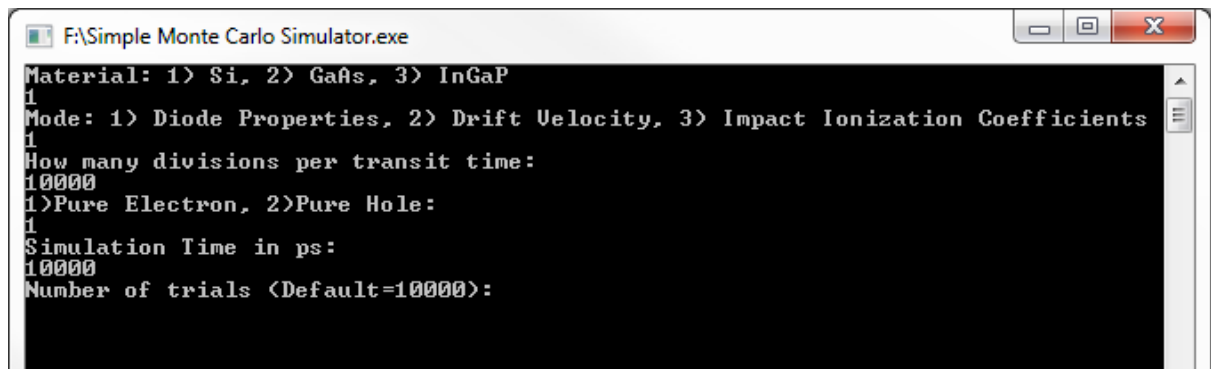


```

F:\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
1
How many divisions per transit time:
10000
1>Pure Electron, 2>Pure Hole:

```

The program will prompt for a simulation time. This is the maximum time from injection of carriers that it will simulate the device for encase not all the carriers have left the device. Typically we specify 1000 ps for this.



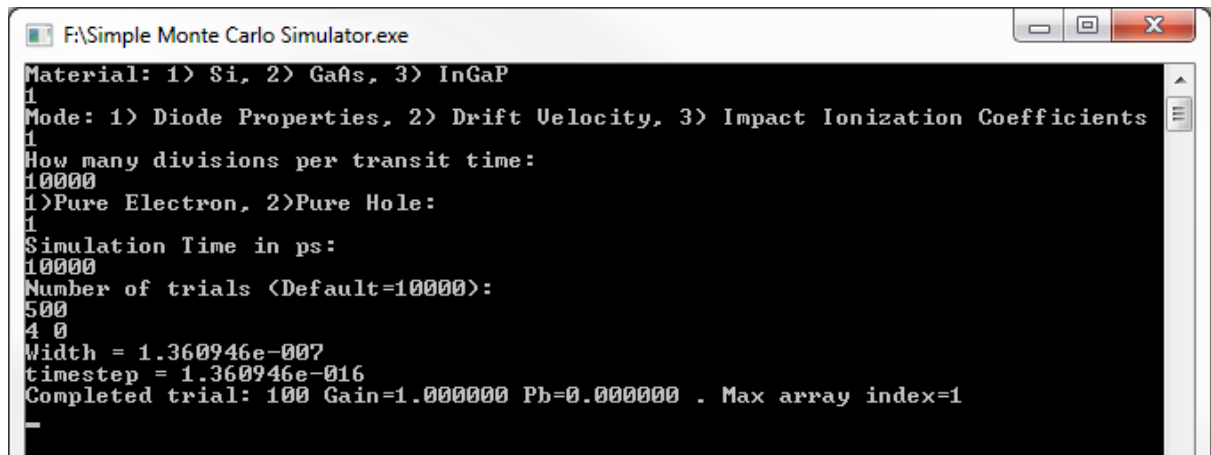
```

F:\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
1
How many divisions per transit time:
10000
1>Pure Electron, 2>Pure Hole:
1
Simulation Time in ps:
10000
Number of trials <Default=10000>:

```

Finally the program will ask for a number of trials per voltage. A Table of typical values is provided below.

Usage	Value
Gain and Excess Noise simulation	10000
Quickly working out breakdown probability	1000
Accurate breakdown probability simulation	10000-20000
Timing Characteristics	20000+



```

F:\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
1
How many divisions per transit time:
10000
1>Pure Electron, 2>Pure Hole:
1
Simulation Time in ps:
10000
Number of trials <Default=10000>:
500
4 0
Width = 1.360946e-007
timestep = 1.360946e-016
Completed trial: 100 Gain=1.000000 Pb=0.000000 . Max array index=1

```

The program will now output the width ( $\mu\text{m}$ ) and the time step size (ps). It will also update the output every 100 trials with the Gain, calculated by counting impact ionization events, the breakdown probability and the Max array index. The max array index is the maximum number of electron hole pairs that have been created at this voltage.

### c) Output files

File Name	Description
<i>scattering_rates.txt</i>	Calculated scattering rates for the material
<i>scattering_pb.txt</i>	Calculated scattering probabilities for the material
<i>Vgain_out.txt</i>	V=simulated voltage, two columns. Column 1 has the trial number, column 2 is the simulated current from Ramos theorem.
<i>Vtime_to_breakdown.txt</i>	V=simulated voltage, two columns. Column 1 has the trial number, column 2 is time (ps) the trial took reach a current threshold of 0.1 m
<i>Veventcounter.txt</i>	Ignore this file
<i>Multiplication.txt</i>	Contains Gain (M), excess noise factor (F) from counting impact ionization events, breakdown probability (Pb) per voltage.
<i>Result.txt</i>	Contains Gain (M), excess noise factor (F) from Ramos theorem and Mean time to breakdown in ps.
<i>VHist.txt</i>	V=simulated voltage, two columns. Column 1 is the central value for the histogram bin (in ps), column 2 contains the number of breakdown events detected in that bin.

### d) Post Processing

Using a script it is possible to extract the timing jitter value from either the *Hist.txt* files or from the raw time to breakdown data in the *time\_to\_breakdown.txt* files.

## 5. Use of Drift Velocity Mode:

### a) Running the Software

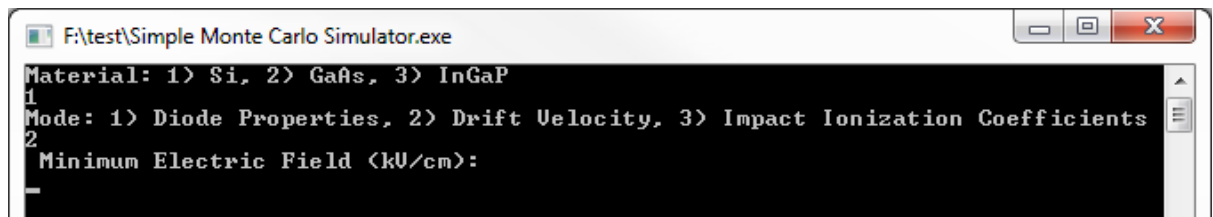
Launch executable

Program will prompt for a material choice.



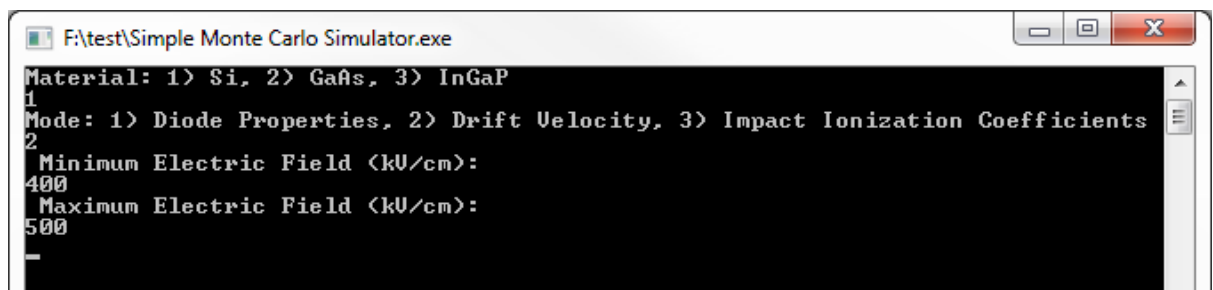
```
F:\Drift_SMC.exe
Material: 1> Si, 2> GaAs, 3> InGaP
_
```

Program will then prompt for a mode choice. Enter 2 for Drift Velocity.



```
F:\test\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
2
Minimum Electric Field (kV/cm):
_
```

Then it will prompt for a minimum electric field, followed by a maximum electric field. Unless the hard coded value has been changed the program will calculate the drift velocity incrementing the electric field between user specified min and max in 1 kV/cm steps.



```
F:\test\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
2
Minimum Electric Field (kV/cm):
400
Maximum Electric Field (kV/cm):
500
_
```

### b) Output files

File Name	Description
<i>scattering_rates.txt</i>	Calculated scattering rates for the material
<i>scattering_pb.txt</i>	Calculated scattering probabilities for the material
<i>velocity.txt</i>	Two Columns. Column 1 is the electric field (kV/cm), column 2 is the drift velocity (m/s).
<i>hvelocity.txt</i>	Two Columns. Column 1 is the electric field (kV/cm), column 2 is the drift velocity (m/s).

## 6. Use of Impact Ionization Coefficient Mode:

### a) Running the Software

Launch executable

Program will prompt for a material choice.

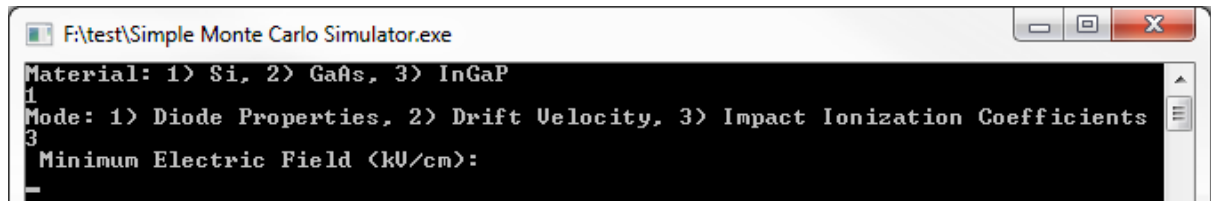


```

F:\Ionization_SMC.exe
Material: 1> Si, 2> GaAs, 3> InGaP

```

Program will then prompt for a mode choice. Enter 3 for Impact Ionization Coefficient Mode.

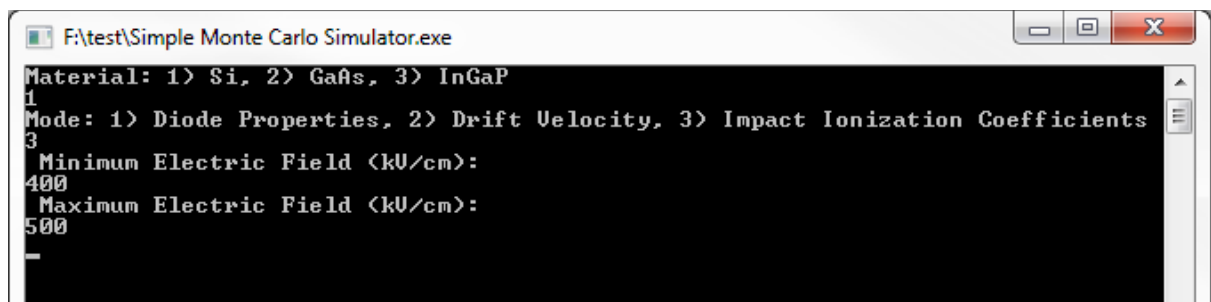


```

F:\test\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
3
Minimum Electric Field (kV/cm):

```

Program will prompt for electric field values then will simulate electric fields in 20kV/cm steps between the minimum and maximum specified value. The simulation will calculate the distance travelled between 20000 consecutive impact ionization events for both electrons and holes.



```

F:\test\Simple Monte Carlo Simulator.exe
Material: 1> Si, 2> GaAs, 3> InGaP
1
Mode: 1> Diode Properties, 2> Drift Velocity, 3> Impact Ionization Coefficients
3
Minimum Electric Field (kV/cm):
400
Maximum Electric Field (kV/cm):
500

```

## b) Output Files

File Name	Description
<i>Fepdf.txt</i>	Contains the electron data, where F is the electric field strength in kV/cm. Contains 2 columns. Column 1 is the impact ionization event number, column 2 is the distance travelled, in meters, since either injection or the previous impact ionization event.
<i>Fhpdf.txt</i>	Contains the hole data, where F is the electric field strength in kV/cm. Contains 2 columns. Column 1 is the impact ionization event number, column 2 is the distance travelled, in meters, since either injection or the previous impact ionization event.
<i>Alpha_beta.txt</i>	Contains three columns. Column 1 Electric Field (kV/cm). Column 2 and 3 are alpha and beta respectively (1/m). Alpha and beta have been calculated as the inverse of the mean distance between consecutive impact ionization events.

## 7. Citations

Please use the following citations for the material parameter sets:

### Silicon

X. Zhou, J. S. Ng, and C. H. Tan, 'A simple Monte Carlo model for prediction of avalanche multiplication process in Silicon', J. Inst., vol. 7, no. 08, p. P08006, 2012. DOI: <https://doi.org/10.1088/1748-0221/7/08/P08006>

#### **Indium Gallium Phosphide**

C. H. Tan, R. Ghin, J. P. R. David, G. J. Rees, and M. Hopkinson, 'The effect of dead space on gain and excess noise in In<sub>0.48</sub>Ga<sub>0.52</sub>P p<sup>+</sup> in<sup>+</sup> diodes', Semiconductor science and technology, vol. 18, no. 8, p. 803, 2003. DOI: <https://doi.org/10.1088/0268-1242/18/8/314>

#### **Gallium Arsenide**

S. A. Plimmer, J. P. R. David, D. S. Ong, and K. F. Li, "A simple model for avalanche multiplication including deadspace effects", IEEE Trans. Electron Devices, vol. 46, no. 4, pp. 769–775, 1999. DOI: <https://doi.org/10.1109/16.753712>